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ON THE ORIGIN OF THE –4.4 eV BAND IN CdTe(100)

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We calculate the bulk- (infinite system), (100)-bulk-projected- and (100)-Surface-projected Green's functions using the Surface Green's Function Matching method (SGFM) and an empirical tight-binding hamiltonian with tight-binding parameters (TBP) that describe well the bulk band structure of CdTe. In particular, we analyze the band (B–4) arising at –4.4 eV from the top of the valence band at Γ according to the results of Niles and Höchst and at -4.6 eV according to Gawlik *et al.* both obtained by Angle-resolved photoelectron spectroscopy (ARPES). We give the first theoretical description of this band.

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